



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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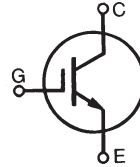
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



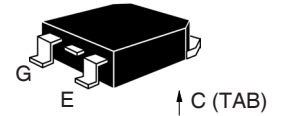
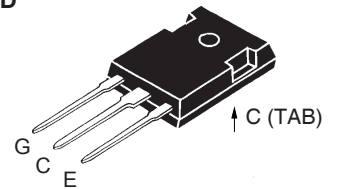
HiPerFAST™ IGBT**IXGH 60N60B2
IXGT 60N60B2**

Optimized for 10-25 kHz hard
switching and up to 100 KHz
resonant switching

$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 75 \text{ A} \\ V_{CE(sat)} &< 1.8 \text{ V} \\ t_{fi\text{typ}} &= 100 \text{ ns} \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$ (limited by leads)	75	A
I_{C110}	$T_C = 110^\circ\text{C}$	60	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	300	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 10 \Omega$ Clamped inductive load @ $\leq 600 \text{ V}$	$I_{CM} = 150$	A
P_C	$T_C = 25^\circ\text{C}$	500	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10 Nm/lb.in.	
Weight	TO-247 AD	6	g
	TO-268 SMD	4	g

**TO-268
(IXGT)****TO-247 AD
(IXGH)**

G = Gate, C = Collector,
E = Emitter, TAB = Collector

Features

- Medium frequency IGBT
- Square RBSOA
- High current handling capability
- MOS Gate turn-on
- drive simplicity

Applications

- PFC circuits
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies
- AC motor speed control
- DC servo and robot drives
- DC choppers

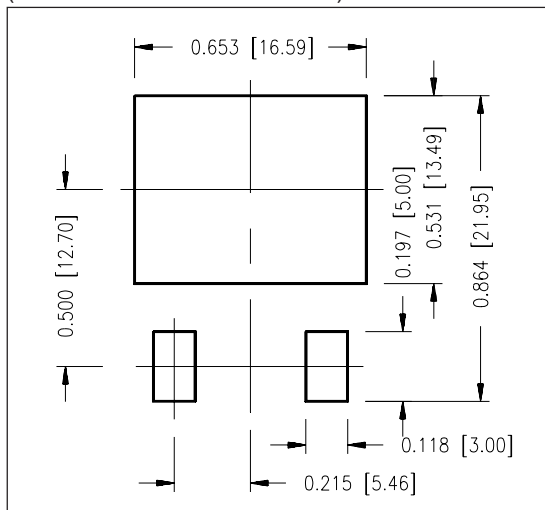
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = 50 \text{ A}, V_{GE} = 15 \text{ V}$ Note 1.			1.8 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$I_C = 50\text{ A}$; $V_{CE} = 10\text{ V}$, Note 1	40	58	S
C_{ies}	$V_{CE} = 25\text{ V}$, $V_{GE} = 0\text{ V}$, $f = 1\text{ MHz}$		3900	pF
C_{oes}			290	pF
C_{res}			100	pF
Q_g	$I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$, $V_{CE} = 0.5 V_{CES}$		170	nC
Q_{ge}			25	nC
Q_{gc}			57	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}$, $R_G = 3.3\ \Omega$ Note 1		28	ns
t_{ri}			30	ns
$t_{d(off)}$			160	270 ns
t_{fi}			100	170 ns
E_{off}			1.0	2.5 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 50\text{ A}$, $V_{GE} = 15\text{ V}$ $V_{CE} = 400\text{ V}$, $R_G = 3.3\ \Omega$ Note 1		28	ns
t_{ri}			36	ns
E_{on}			0.6	mJ
$t_{d(off)}$			310	ns
t_{fi}			240	ns
E_{off}			2.8	mJ
R_{thJC}			0.15	0.25 KW/KW
R_{thCK}				

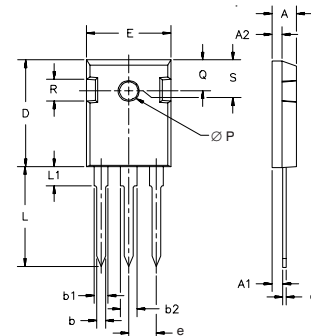
Notes:

1. Pulse test, $t < 300\mu\text{s}$ wide, duty cycle $< 2\%$.

Min. Recommended Footprint (Dimensions in inches and mm)

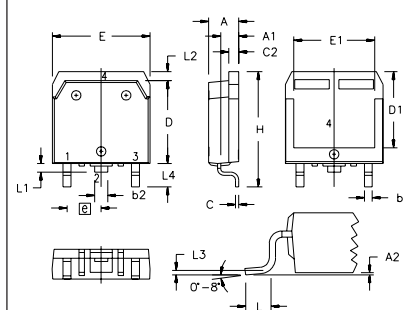


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C ₂	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D ₁	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E ₁	.524	.535	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L ₁	.047	.055	1.20	1.40
L ₂	.039	.045	1.00	1.15
L ₃	.010	BSC	0.25	BSC
L ₄	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

Fig. 1. Output Characteristics
@ 25 Deg. C

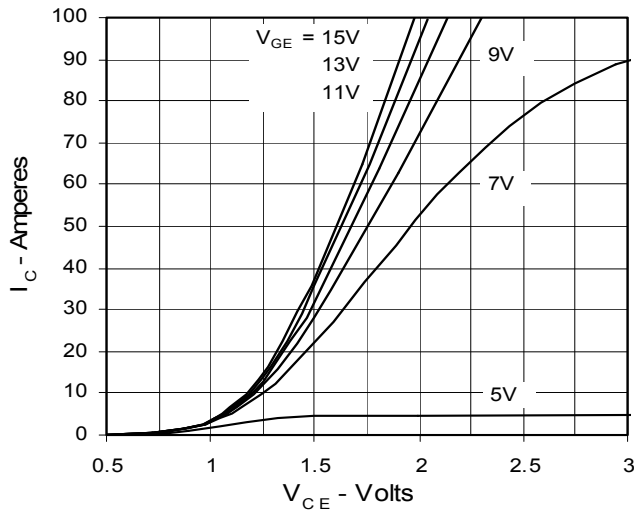


Fig. 2. Extended Output Characteristics
@ 25 deg. C

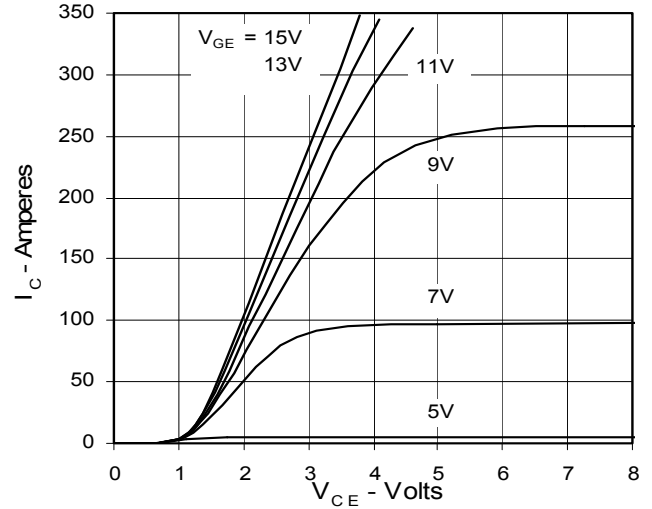


Fig. 3. Output Characteristics
@ 125 Deg. C

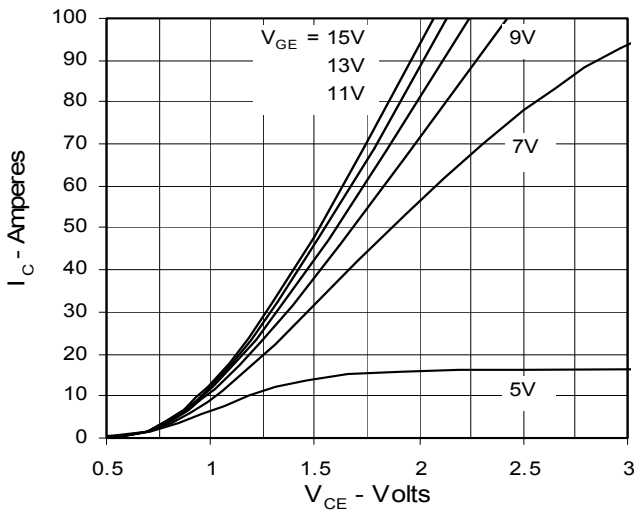


Fig. 4. Dependence of $V_{CE(sat)}$ on Temperature

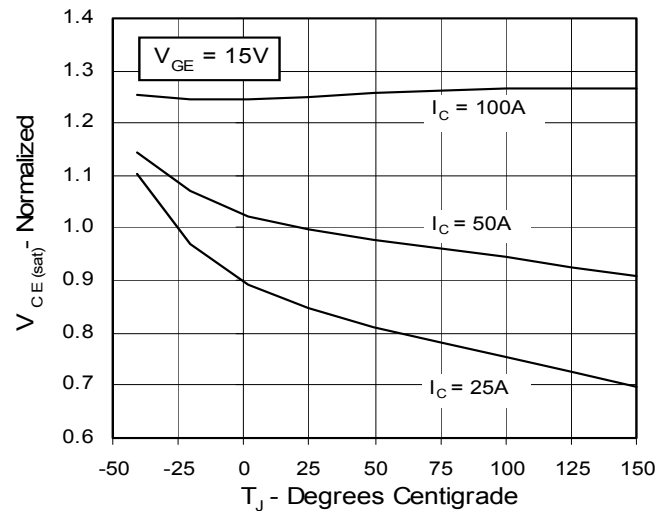


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter voltage

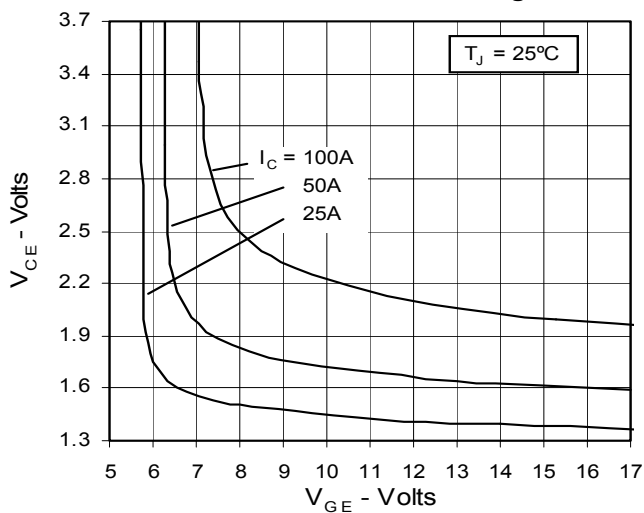


Fig. 6. Input Admittance

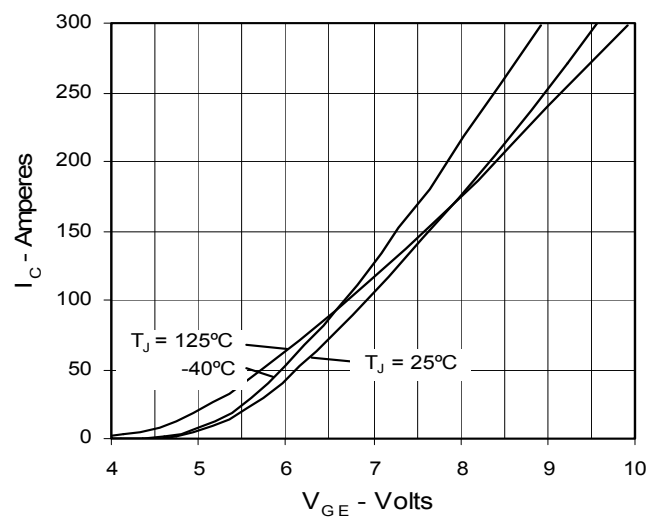


Fig. 7. Transconductance

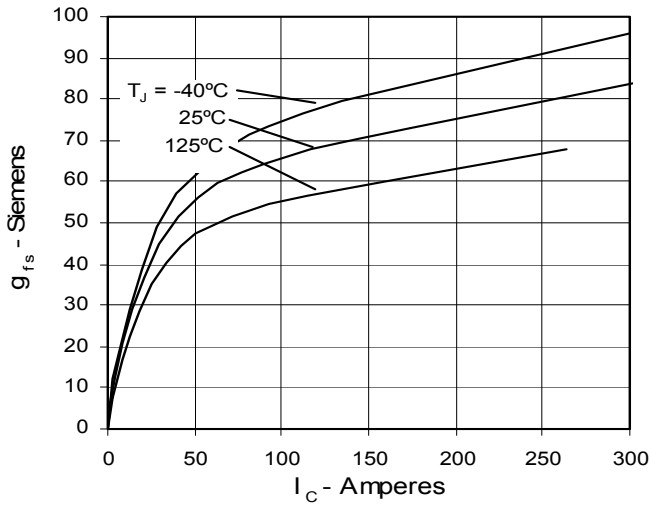


Fig. 8. Dependence of Turn-Off Energy on R_G

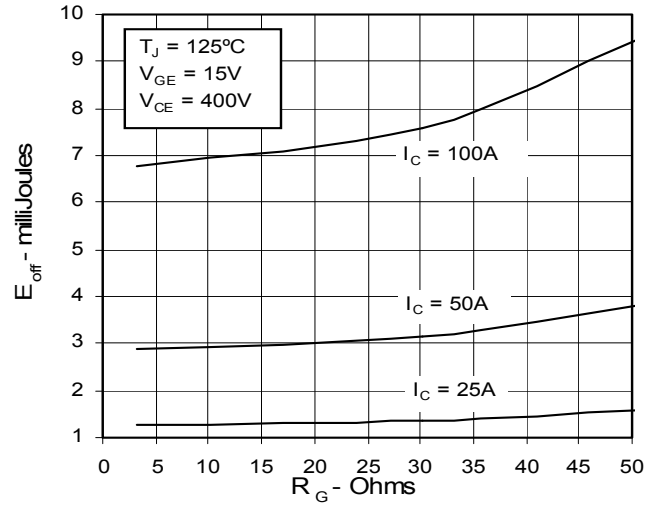


Fig. 9. Dependence of Turn-Off Energy on I_C

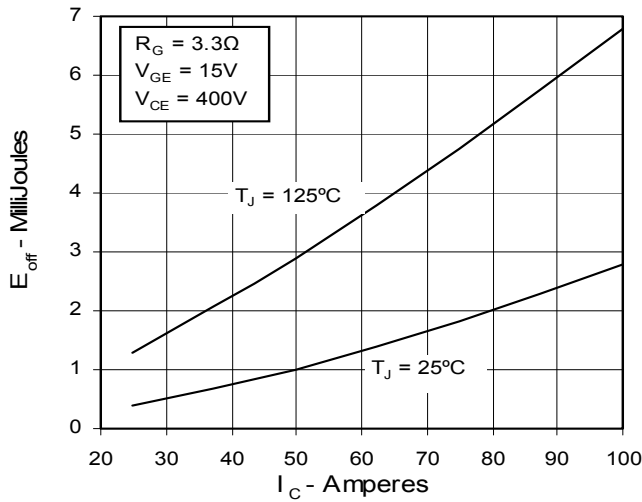


Fig. 10. Dependence of Turn-Off Energy on Temperature

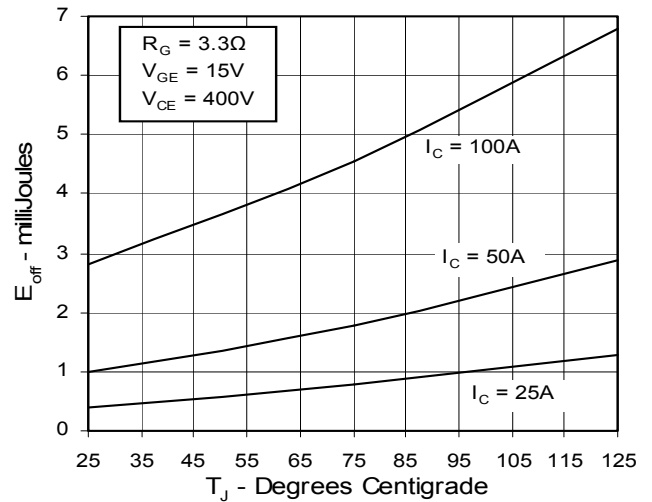


Fig. 11. Dependence of Turn-Off Switching Time on R_G

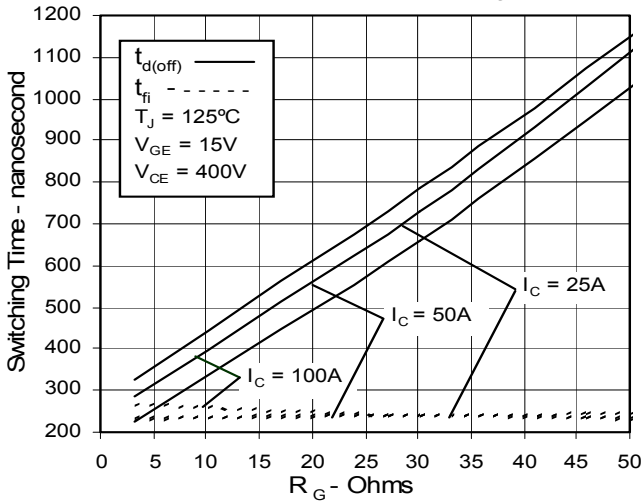


Fig. 12. Dependence of Turn-Off Switching Time on I_C

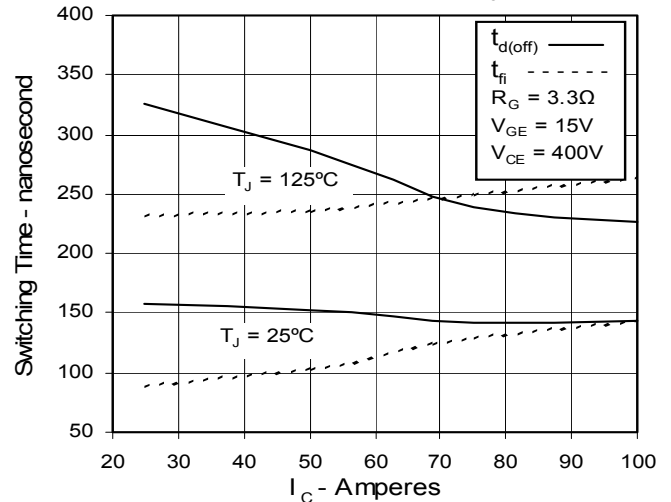
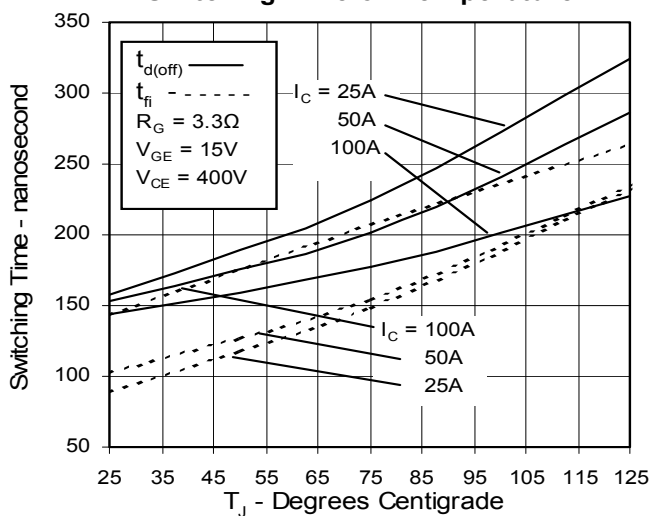
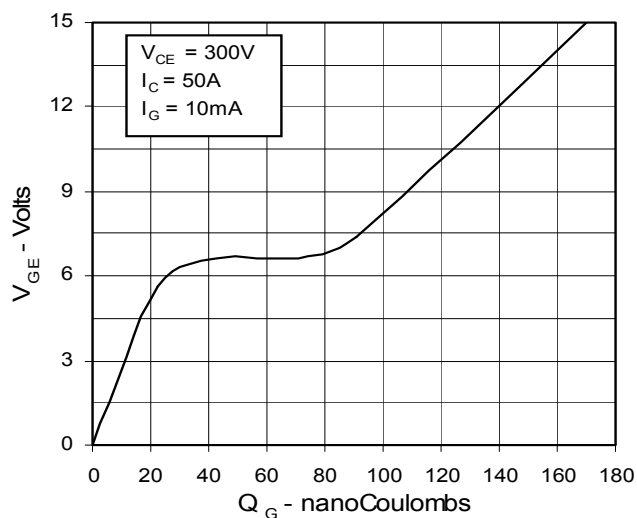
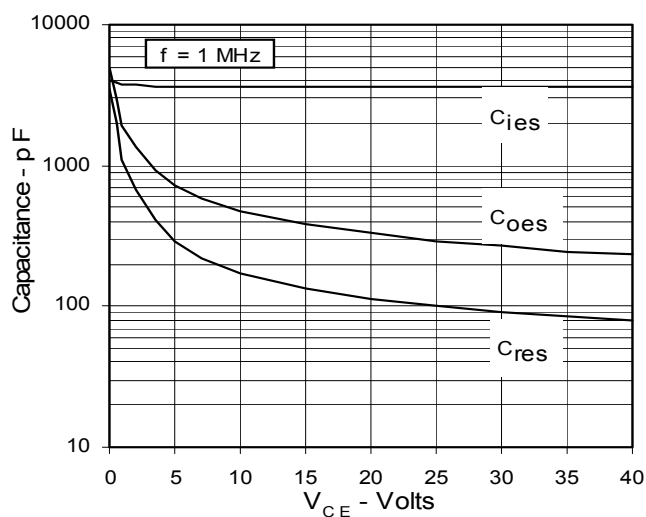


Fig. 13. Dependence of Turn-Off Switching Time on Temperature

Fig. 14. Gate Charge

Fig. 15. Capacitance

Fig. 16. Maximum Transient Thermal Resistance
